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INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(S1) International Patent Classification 7 : G01T 1/20		A1	(11) International Publication Number: WO 00/43810 (43) International Publication Date: 27 July 2000 (27.07.00)
(21) International Application Number: PCT/SE00/00135		(81) Designated States: AB, AL, AM, AT, AT (Utility model), AU, AZ, BA, BB, BG, BR, BY, CA, CE, CN, CR, CU, CZ, CZ (Utility model), DE, DE (Utility model), DK, DK (Utility model), DM, EE, EE (Utility model), ES, FI, FI (Utility model), GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KR (Utility model), KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, US, UZ, VN, YU, ZA, ZW, ARIPO patent (GH, GM, KE, LS, MW, SD, SL, SZ, TZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG).	
(22) International Filing Date: 21 January 2000 (21.01.00)		Published <i>With international search report. Before the expiration of the time limit for amending the claims and to be republished in the event of the receipt of amendments.</i>	
(30) Priority Data: 9900181-0 21 January 1999 (21.01.99) SE			
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(54) Title: X-RAY PIXEL DETECTOR DEVICE AND FABRICATION METHOD			
(57) Abstract			
<p>A method and a device are disclosed for producing an X-ray pixel detector, i.e. an imaging detector for X-ray photons, the detector presenting high efficiency combined with high resolution for obtaining a high image quality detector while at the same time minimizing the X-ray dose used. The application is particularly important whenever the X-ray photon absorption distance is much longer than the required pixel size. The arrangement according to the present invention presents a structure based on light-guiding of secondarily produced photons within a scintillating pixel detector in conjunction with, a CCD or a CMOS pixel detector. The structure according to the invention presents a matrix (8) having deep pores (10) fabricated by high-aspect ratio silicon etching techniques producing very thin walls and with a pore spacing less or equal to the size of a pixel (2) of the image detector used. The pore matrix is subsequently filled by injecting a scintillating material into the pores such that, in each pore, a single scintillating block is formed. The silicon matrix (8) may further utilize a reflective layer to increase light guiding down to the image detector chip.</p>			